

FIG. 1

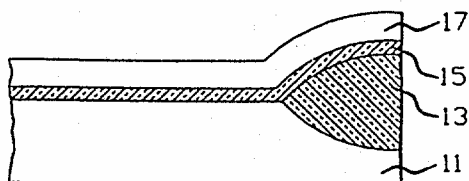


FIG. 2

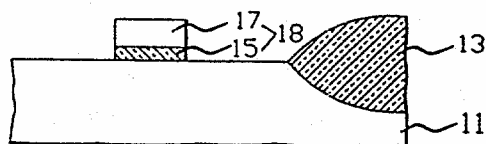


FIG. 3

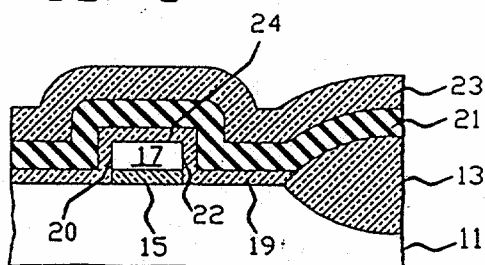


FIG. 4

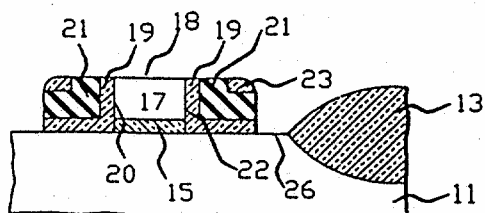


FIG. 5

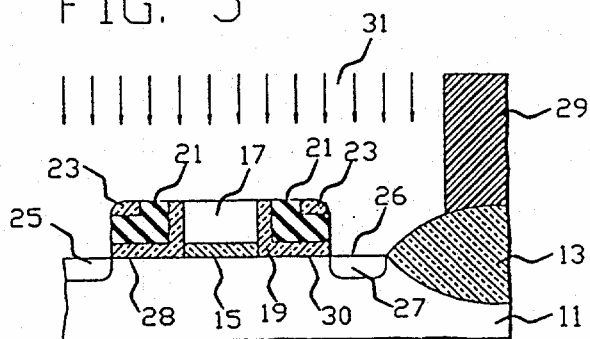


FIG. 6

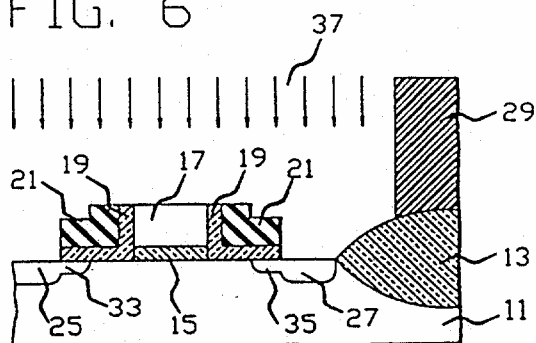


FIG. 7

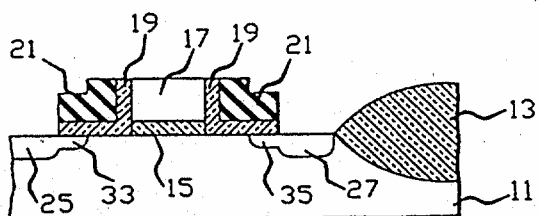


FIG. 8

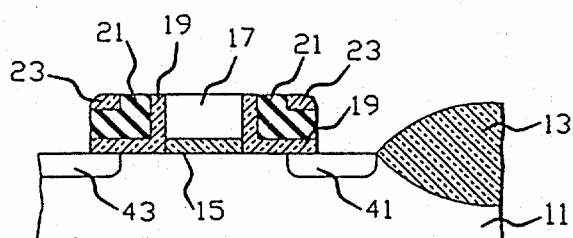


FIG. 9

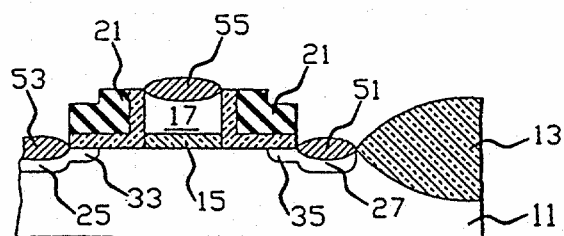


FIG. 10

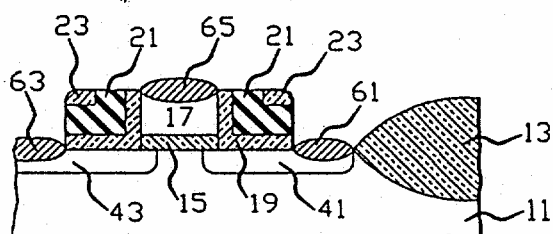


FIG. 11

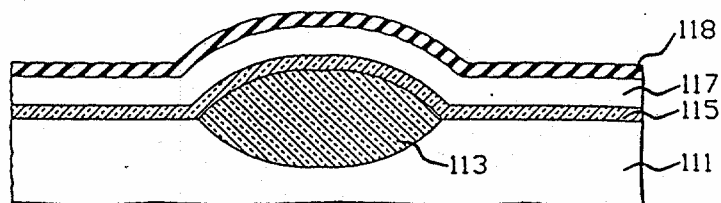


FIG. 12

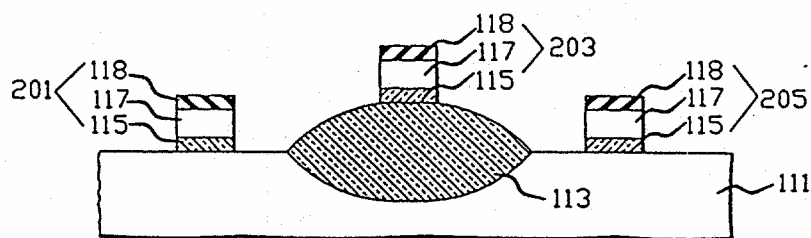


FIG. 13

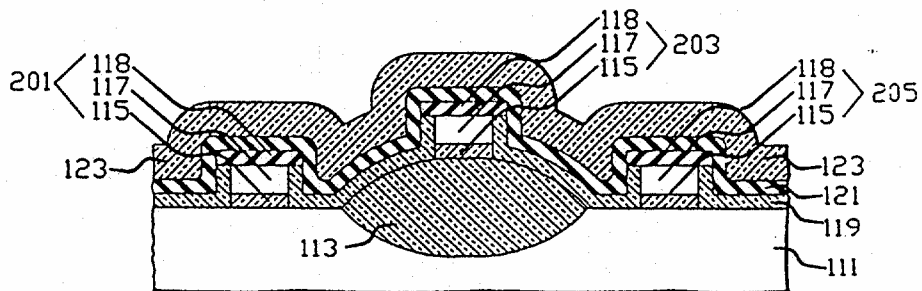
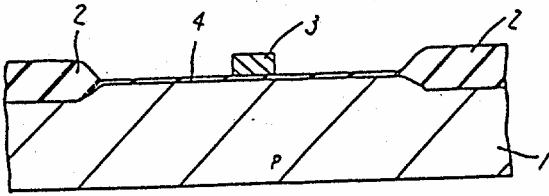


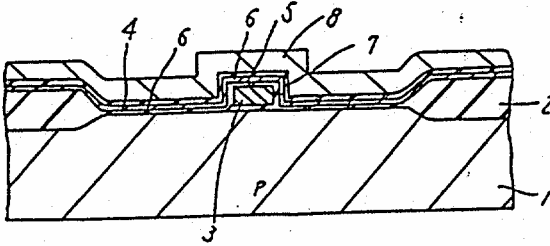
FIG. 1 is a cross-sectional view of a semiconductor device. The device is built on a substrate 111. A central region 113 is defined on the substrate, and side regions 115 are located on either side of the central region. A central layer 118 is formed on the central region 113, and a central block 117 is formed on top of the central layer 118. Side regions 119 are formed on the side regions 115, and side blocks 117 are formed on top of the side regions 119. The central block 117 and the side blocks 117 are connected by a central layer 118. Various layers and structures are labeled with numbers 121, 123, 170, and 118.

Figure 1 is a schematic representation of the experimental design. It shows a sequence of three boxes connected by arrows. The first box is labeled 'Stimulus' and contains the word 'cat'. An arrow points from this box to a second box labeled 'Response', which contains the word 'cat'. Another arrow points from the second box to a third box labeled 'Feedback', which contains the word 'cat'.

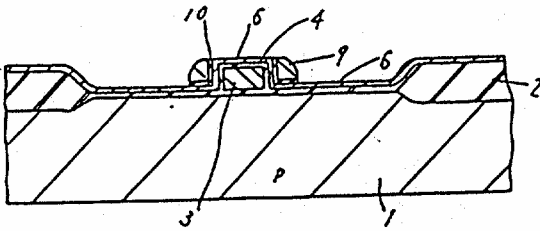
第 1 圖



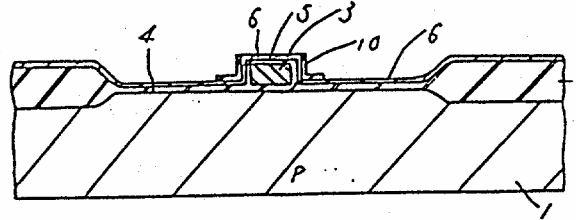
第 2 図



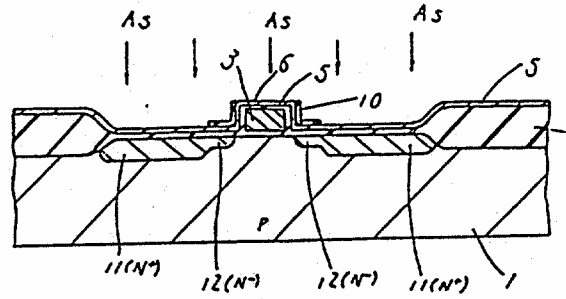
第 3 圖



第 4 圖



第 5 圖



第 6 図

